RT3TDDU

Composite Transistor With Resistor For Switching Application Silicon Epitaxial Type

DESCRIPTION

RT3TDDU is a composite transistor built with two RT1N237 chip and RT1P237 chip in SC-75A package.

FEATURE

Silicon epitaxial type

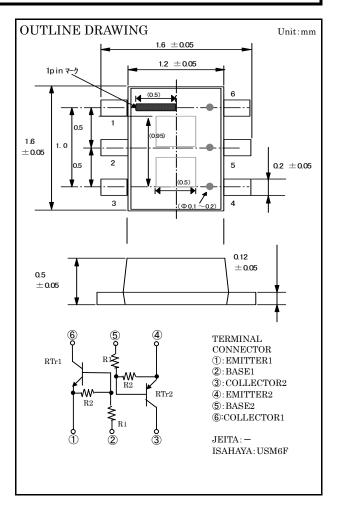
Each transistor elements are independent.

Mini package for easy mounting

APPLICATION

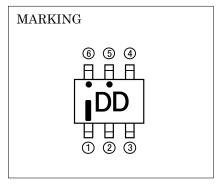
Inverted circuit, switching circuit, interface circuit, driver circuit

XPNP built in transistor of "-"sign is abbreviation.



MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING	UNIT	
Vcbo	Collector to Base voltage	50	V	
VEBO	Emitter to Base voltage	6	V	
$V_{\rm CEO}$	Collector to Emitter voltage	50	V	
VIN	Input Voltage	12	V	
Ic	Collector current	100	mA	
ICM	Peak Collector current	200	mA	
Pc	Collector dissipation (Total, Ta=25°C)	125	mW	
Tj	Junction temperature	+150	°C	
T_{stg}	Storage temperature	-55~+150	°C	





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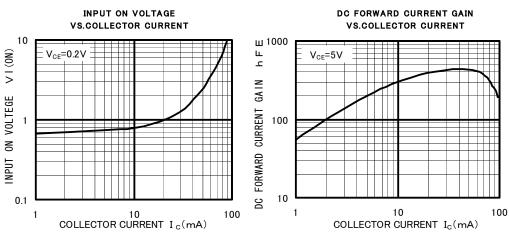
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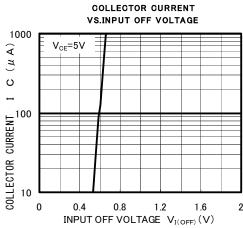
Composite Transistor With Resistor For Switching Application Silicon Epitaxial Type

ELECTRICAL	CHARACTERISTICS (Ta=25°C)	(Tr1 Tr2 common)
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Symbol	Parameter	m , 1:::	Limits			TT 11	
		Test conditions		Min	Тур	Max	Unit
V(BR)CEO	Collector to Emitter break down voltage	I c=100μA, R _{BE} =∞		50			V
ICBO	Collector cut off current	V _{CB} =50V, I _E =0				0.1	μA
hFE	DC forward current gain	V _{CE} =5V, I C=10mA		80			-
VCE(sat)	Collector to Emitter saturation voltage	I $_{\rm C}$ =10mA, I $_{\rm B}$ =0.5mA			0.1	0.3	V
VI(ON)	Input on voltage	V _{CE} =0.2V, I _C =5mA			0.7	1.1	V
VI(OFF)	Input off voltage	V _{CE} =5V, I _C =100μA		0.5	0.6		V
R ₁	Input resistor			1.5	2.2	2.9	ΚΩ
R ₂ /R ₁	Resistor ratio			17	22	26	-
f_{T}	Gain band width product	Tr1	V _{CE} =6V, I _E =-10mA		200		MHz
		Tr2	V_{CE} =-6 V , I_{E} =10 mA		150		

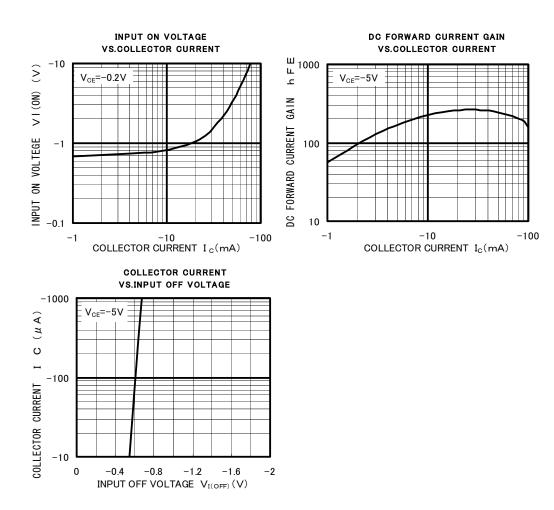
TYPICAL CHARACTERISTICS (Tr1)





ISAHAYA ELECTRONICS CORPORATION

TYPICAL CHARACTERISTICS (Tr2)





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